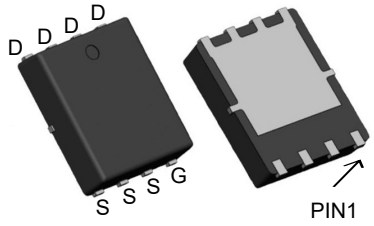
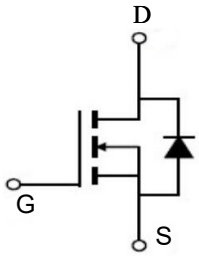
General Description

The MY80N03NE3 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

Features

V_{DSS}	30	V
I_D	80	A
$R_{DS(ON)}$(atV_{GS}=10V)	3.4	mΩ
$R_{DS(ON)}$(atV_{GS}=4.5V)	4.0	mΩ





Application

- Battery protection
- Load switch
- Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY80N03NE3	PDFN3*3-8	MY80N03NE3	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	80	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	50	A
I_{DM}	Pulsed Drain Current[2]	160	A
EAS	Single Pulse Avalanche Energy[3]	144.7	mJ
I_{AS}	Avalanche Current	53.8	A
P_D@T_C=25℃	Total Power Dissipation[4]	43.4	W
P_D@T_A=25℃	Total Power Dissipation[4]	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	75	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	30	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	2.88	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.0213	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	3.2	4.7	mΩ
		V_{GS}=4.5V , I_D=15A	---	4.0	6	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.5	V
$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.73	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	26.5	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.4	---	
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=12A	---	31.6	---	nC
Q_{gs}	Gate-Source Charge		---	6.07	---	
Q_{gd}	Gate-Drain Charge		---	13.8	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=1.5 I_D=20A	---	11.2	---	ns
T_r	Rise Time		---	49	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
T_f	Fall Time		---	7.8	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1260	---	pF
C_{oss}	Output Capacitance		---	139	---	
C_{rss}	Reverse Transfer Capacitance		---	98	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	80	A
I_{SM}	Pulsed Source Current[2,5]		---	---	160	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :
1.The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V DD =25V,V GS =10V,L=0.1mH,I AS =53.8A
4.The power dissipation is limited by 175℃ junction temperature
5.The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.
6.Package limitation current is 85A.

Typical Characteristics

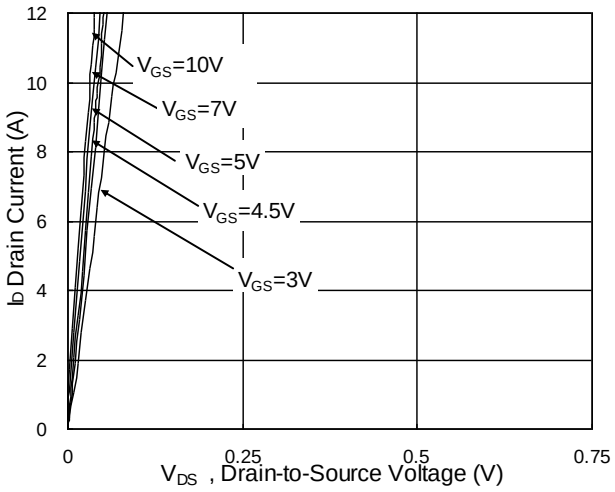


Fig.1 Typical Output Characteristics

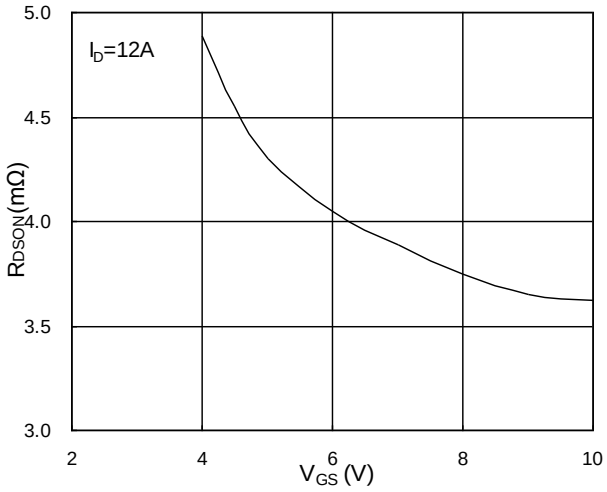


Fig.2 On-Resistance vs. G-S Voltage

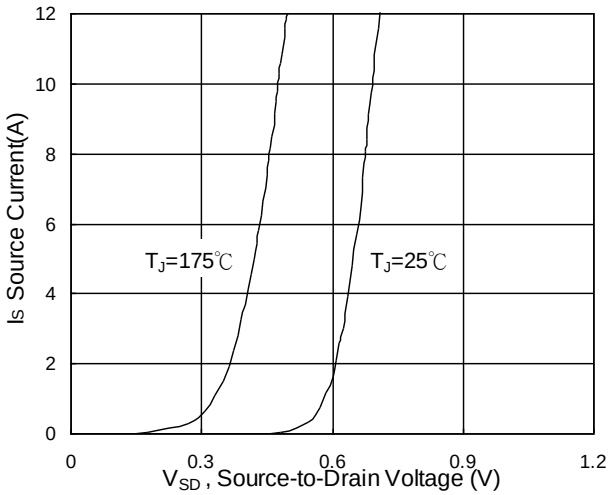


Fig.3 Forward Characteristics of Reverse

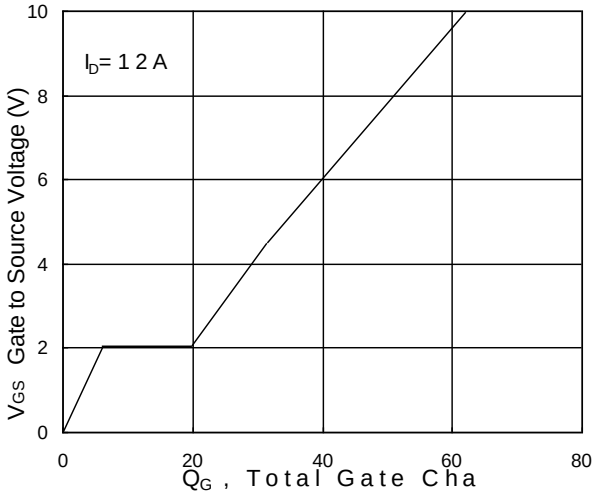


Fig.4 Gate-Charge Characteristics

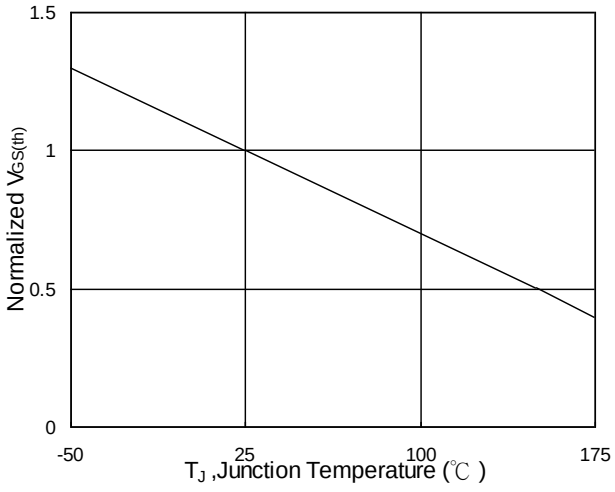


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

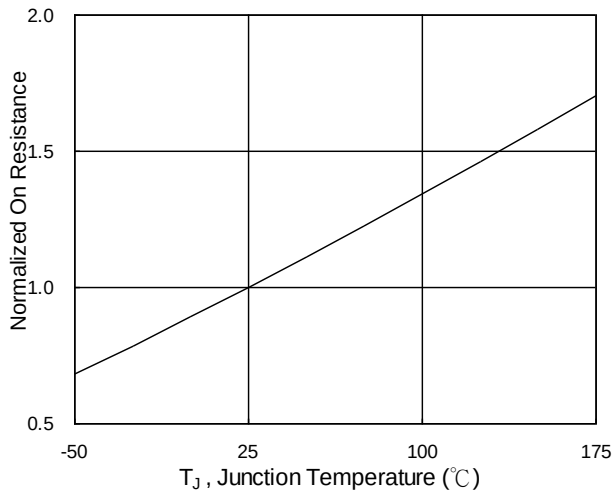


Fig.6 Normalized R_{DSON} vs. T_J

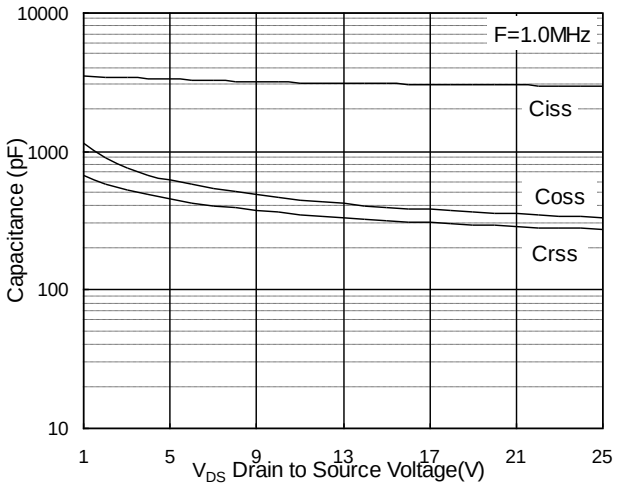


Fig.7 Capacitance

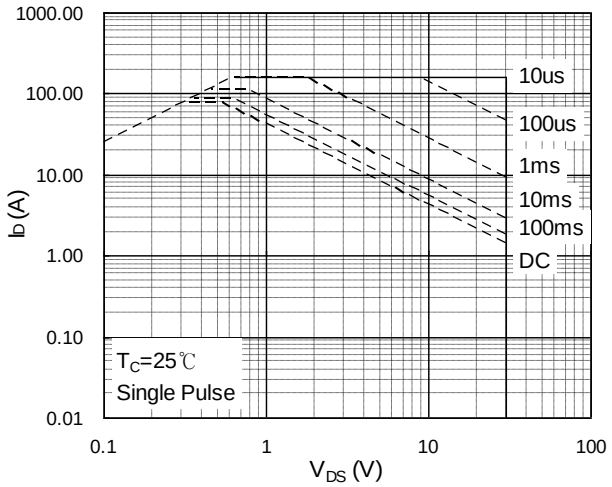


Fig.8 Safe Operating Area

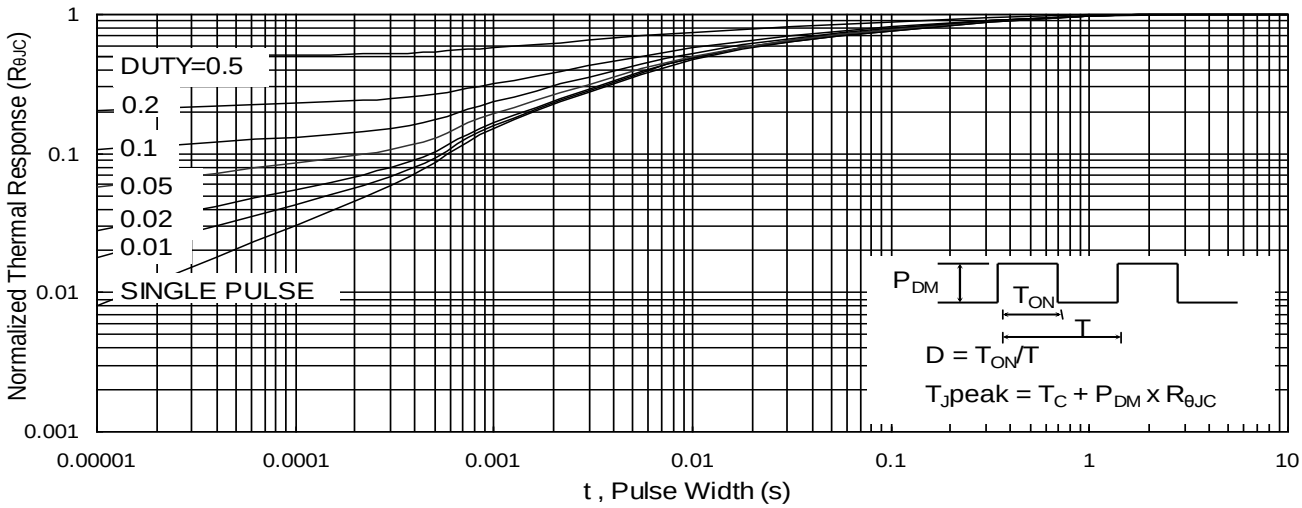


Fig.9 Normalized Maximum Transient Thermal Impedance

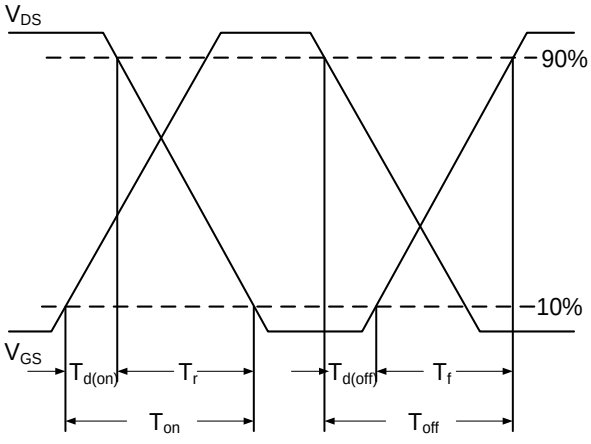


Fig.10 Switching Time Waveform

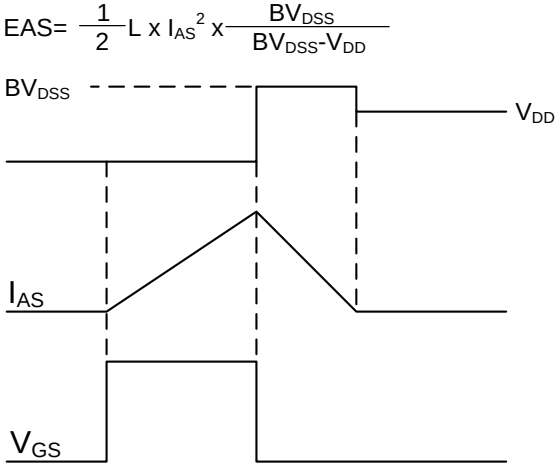
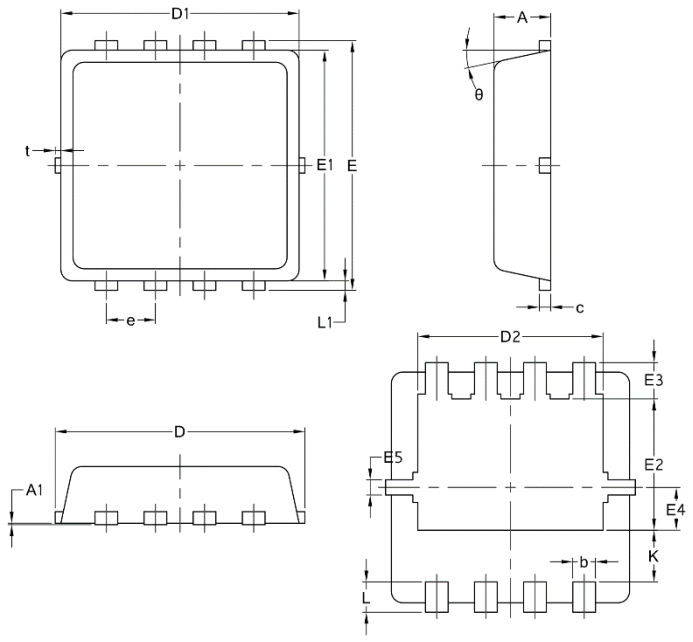


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-DFN3*3-8L-JQ Single



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14